

1. Record Nr.	UNINA9910870868603321
Autore	Maiti C. K
Titolo	Strain-Engineered MOSFETs / C. K. Maiti, T. K. Maiti
Pubbl/distr/stampa	Boca Raton : , : CRC Press, , 2012
Descrizione fisica	1 online resource (1 p.)
Soggetti	Technology & Engineering / Electronics / Microelectronics Technology
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Sommario/riassunto	This book brings together new developments in the area of strain-engineered MOSFETs using high-mobility substrates such as SiGe, strained-Si, germanium-on-insulator and III-V semiconductors into a single text which will cover the materials aspects, principles, and design of advanced devices, their fabrication and applications. The book presents a full TCAD methodology for strain-engineering in Si CMOS technology involving data flow from process simulation to systematic process variability simulation and generation of SPICE process compact models for manufacturing for yield optimization.